

Notice of References Cited	Application/Control No. 10/530,883	Applicant(s)/Patent Under Reexamination SUGAWARA, YOSHITAKA	
	Examiner A. Sefer	Art Unit 2826	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-2005/0184296	08-2005	Sudarshan et al.	257/077
*	B	US-6,252,250	06-2001	Harris et al.	257/77
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 9-148681	06-1997	Japan	Tatao	
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Ivanov et al., "Recent developments in SiC single-crystal electronics," Semiconductor Sci. Technol. 7 (1992)
	V	Danielsson et al., "Investigation of thermal properties in fabricated 4H-SiC high power bipolar transistors," Science Direct (January 2003)
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.